

XP133A1235SR



Power MOS FET

- ◆N-Channel Power MOS FET
- ◆DMOS Structure
- ◆Low On-State Resistance : 0.035Ω (max)
- ◆Ultra High-Speed Switching
- ◆SOP-8 Package
- ◆Two FET Devices Built-in

General Description

The XP133A1235SR is an N-Channel Power MOS FET with low on-state resistance and ultra high-speed switching characteristics.

Two FET devices are built into the one package.

Because high-speed switching is possible, the IC can be efficiently set thereby saving energy.

The small SOP-8 package makes high density mounting possible.

Applications

- Notebook PCs
- Cellular and portable phones
- On-board power supplies
- Li-ion battery systems

Features

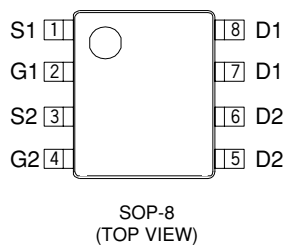
Low on-state resistance : $R_{ds(on)} = 0.035\Omega$ ($V_{gs} = 4.5V$)
 : $R_{ds(on)} = 0.048\Omega$ ($V_{gs} = 2.5V$)

Ultra high-speed switching

Operational Voltage : 2.5V

High density mounting : SOP-8

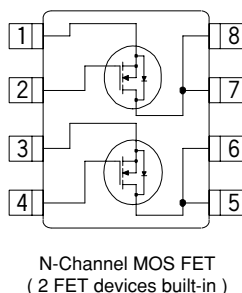
Pin Configuration



Pin Assignment

PIN NUMBER	PIN NAME	FUNCTION
1	S1	Source
2	G1	Gate
3	S2	Source
4	G2	Gate
5~6	D2	Drain
7~8	D1	Drain

Equivalent Circuit



Absolute Maximum Ratings

$T_a = 25^\circ C$

PARAMETER	SYMBOL	RATINGS	UNITS
Drain - Source Voltage	V_{dss}	20	V
Gate - Source Voltage	V_{gss}	± 12	V
Drain Current (DC)	I_d	6	A
Drain Current (Pulse)	I_{dp}	20	A
Reverse Drain Current	I_{dr}	6	A
Continuous Channel Power Dissipation (note)	P_d	2	W
Channel Temperature	T_{ch}	150	$^\circ C$
Storage Temperature	T_{stg}	- 55 ~ 150	$^\circ C$

(note) : When implemented on a glass epoxy PCB

Electrical Characteristics

DC Characteristics

						Ta=25°C
PARAMETER	SYMBOL	CONDITIONS	MIN	TYP	MAX	UNITS
Drain Cut-off Current	Idss	Vds = 20V , Vgs = 0V			10	μA
Gate-Source Leakage Current	Igss	Vgs = ± 12V , Vds = 0V			±1	μA
Gate-Source Cut-off Voltage	Vgs (off)	Id = 1mA , Vds = 10V	0.5		1.2	V
Drain-Source On-state Resistance (note)	Rds (on)	Id = 3A , Vgs = 4.5V		0.026	0.035	Ω
		Id = 3A , Vgs = 2.5V		0.035	0.048	Ω
Forward Transfer Admittance (note)	Yfs	Id = 4A , Vds = 10V		14		S
Body Drain Diode Forward Voltage	Vf	If = 7A , Vgs = 0V		0.85	1.1	V

(note) : Effective during pulse test.

Dynamic Characteristics

						Ta=25°C
PARAMETER	SYMBOL	CONDITIONS	MIN	TYP	MAX	UNITS
Input Capacitance	Ciss	Vds = 10V , Vgs = 0V f = 1 MHz		760		pF
Output Capacitance	Coss			430		pF
Feedback Capacitance	Crss			200		pF

Switching Characteristics

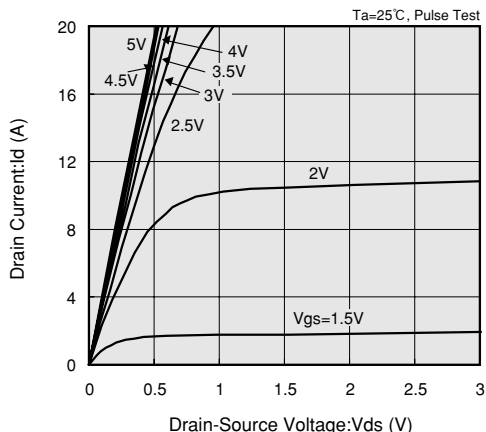
						Ta=25°C
PARAMETER	SYMBOL	CONDITIONS	MIN	TYP	MAX	UNITS
Turn-on Delay Time	td (on)	Vgs = 5V , Id = 3A Vdd = 10V		10		ns
Rise Time	tr			20		ns
Turn-off Delay Time	td (off)			55		ns
Fall Time	tf			15		ns

Thermal Characteristics

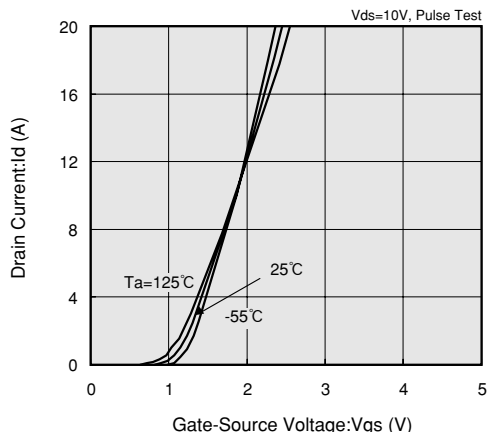
PARAMETER	SYMBOL	CONDITIONS	MIN	TYP	MAX	UNITS
Thermal Resistance (channel-ambience)	Rth (ch-a)	Implement on a glass epoxy resin PCB		62.5		°C / W

Typical Performance Characteristics

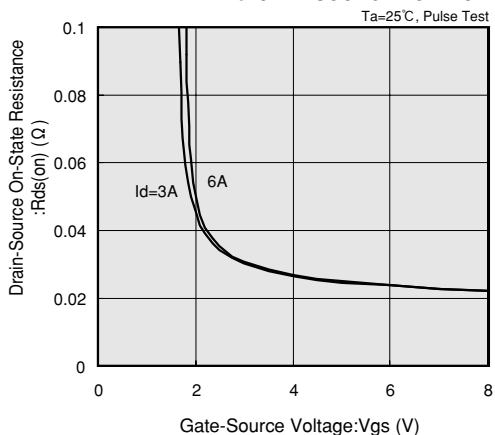
DRAIN CURRENT vs. DRAIN-SOURCE VOLTAGE



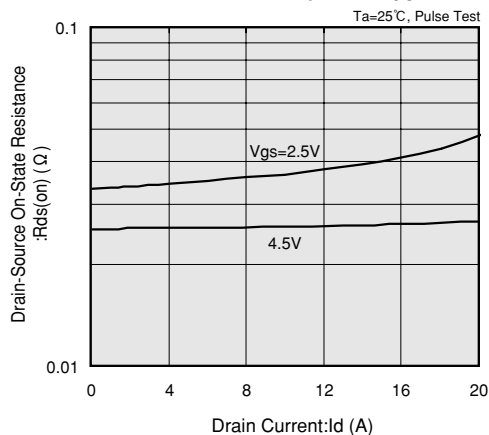
DRAIN CURRENT vs. GATE-SOURCE VOLTAGE



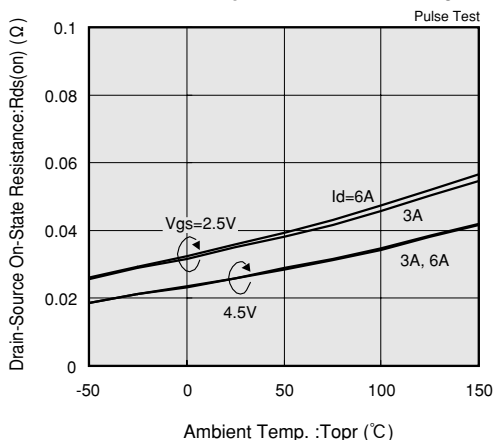
DRAIN-SOURCE ON-STATE RESISTANCE vs. GATE-SOURCE VOLTAGE



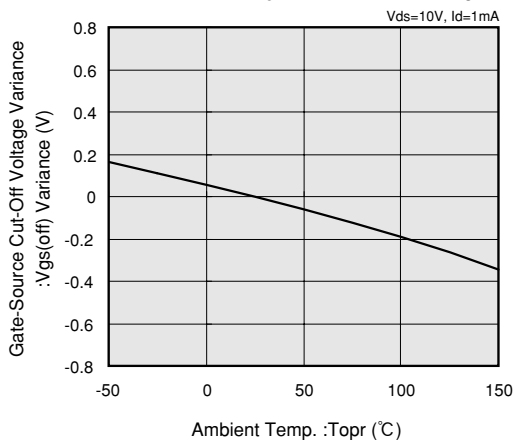
DRAIN-SOURCE ON-STATE RESISTANCE vs. DRAIN CURRENT



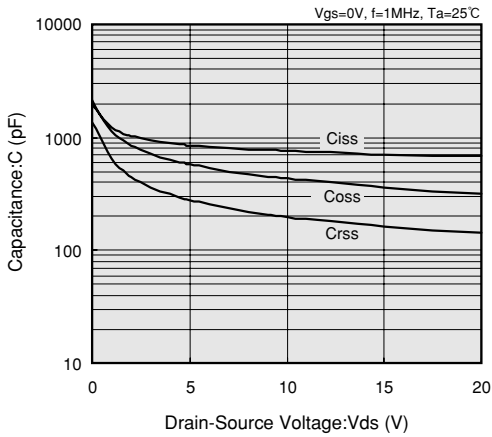
DRAIN-SOURCE ON-STATE RESISTANCE vs. AMBIENT TEMPERATURE



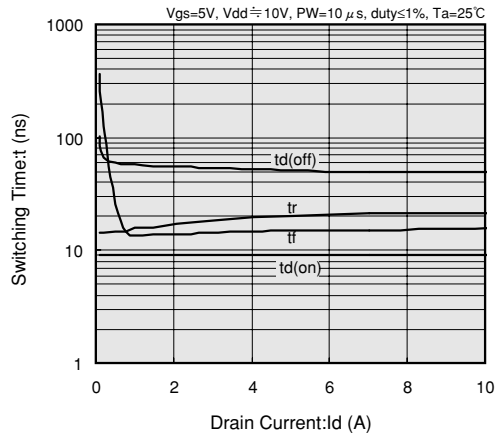
GATE-SOURCE CUT-OFF VOLTAGE VARIANCE vs. AMBIENT TEMPERATURE



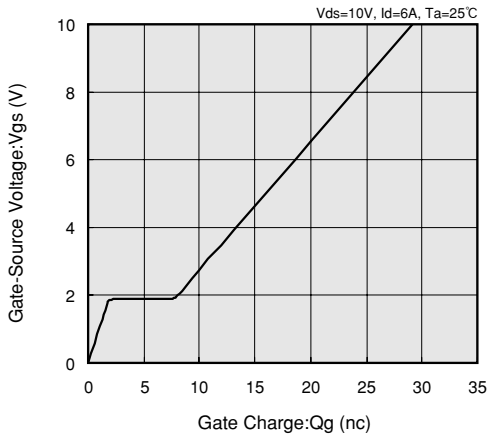
CAPACITANCE vs. DRAIN-SOURCE VOLTAGE



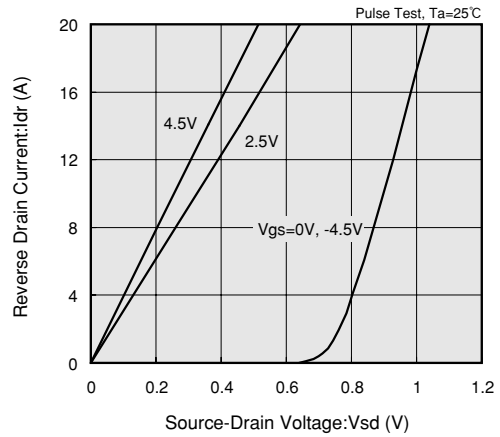
SWITCHING TIME vs. DRAIN CURRENT



GATE-SOURCE VOLTAGE vs. GATE CHARGE



REVERSE DRAIN CURRENT vs. SOURCE-DRAIN VOLTAGE



STANDARDIZED TRANSITION THERMAL RESISTANCE vs. PULSE WIDTH

